

## Plastic-Encapsulate Transistors

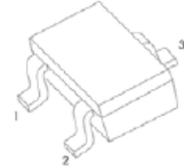
TRANSISTOR (NPN)

### FEATURES

Complimentary to SS8550T

### MARKING: Y1

#### SOT-523



1. BASE
2. EMITTER
3. COLLECTOR

### MAXIMUM RATINGS ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	40	V
$V_{CEO}$	Collector-Emitter Voltage	25	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	1.5	A
$P_C$	Collector Power Dissipation	0.2	W
$T_J$	Junction Temperature	-55-150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$ , $I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}$ , $I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$ , $I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40\text{V}$ , $I_E=0$			0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CB}=20\text{V}$ , $I_E=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}$ , $I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}$ , $I_C=100\text{mA}$	120		400	
	$h_{FE(2)}$	$V_{CE}=1\text{V}$ , $I_C=800\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800\text{mA}$ , $I_B=80\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800\text{mA}$ , $I_B=80\text{mA}$			1.2	V
Transition frequency	$f_T$	$V_{CE}=10\text{V}$ , $I_C=50\text{mA}$ $f=30\text{MHz}$	100			MHz

### CLASSIFICATION OF $h_{FE(1)}$

RANK	L	H	J
RANGE	120 - 200	200 - 350	300 - 400

## Typical Characteristics

